

## **isc Silicon NPN Power Transistor**

## 2SC5802

### DESCRIPTION

- · High Breakdown Voltage-
- : V<sub>CBO</sub>= 1500V (Min)
- High Switching Speed
- Wide Area of Safe Operation
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

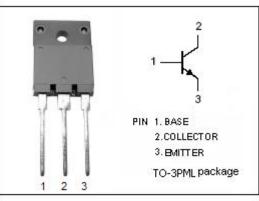
### **APPLICATIONS**

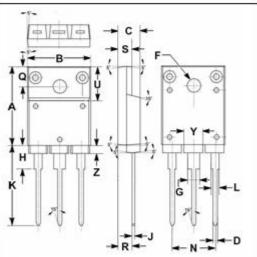
• Designed for high voltage color display horizontal deflection output applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)							
SYMBOL	PARAMETER	VALUE	UNIT				
V <sub>CBO</sub>	Collector-Base Voltage	1500	V				
V <sub>CEO</sub>	Collector-Emitter Voltage	800	V				
V <sub>EBO</sub>	Emitter-Base Voltage	6	V				
lc	Collector Current- Continuous	10	A				
I <sub>CM</sub>	Collector Current- Peak	30	A				
Pc	Collector Power Dissipation @ $T_C$ =25°C	60	W				
TJ	Junction Temperature	150	°C				
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C				
I stg	Storage Temperature Range	-55~150					

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### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)





	mm	
DIM	MIN	MAX
Α	19.90	20.10
В	15.90	16.10
С	5.50	5.70
D	0.90	1.10
F	3.30	3.50
G	2.90	3.10
Н	5.90	6.10
J	0.595	0.605
К	22.30	22.50
L	1.90	2.10
Ν	10.80	11.00
Q	4.90	5.10
R	3.75	3.95
S	3.20	3.40
U	9.90	10.10
Υ	4.70	4.90
Z	1.90	2.10

isc Website: www.iscsemi.cn



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### **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 6A; I <sub>B</sub> = 1.5A			3.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 6A; I <sub>B</sub> = 1.5A			1.5	V
Ices	Collector Cutoff Current	V <sub>CE</sub> = 1400V; V <sub>BE</sub> = 0			1.0	mA
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 800V; I <sub>E</sub> = 0			10	μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 4V; I <sub>C</sub> = 0			1.0	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V	15		48	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 6A; V <sub>CE</sub> = 5V	7		10	
t <sub>f</sub>	Fall Time	I <sub>C</sub> = 6A, I <sub>B1</sub> = 1.2A; I <sub>B2</sub> = -2.4A; V <sub>CC</sub> = 200V; RL= 33.3 Ω			0.3	μ <b>S</b>

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